Microsemi Corp.
The diode experts

ALSO AVAILABLE IN SURFACE MOUNT

IN4500 and IN4500-1

SANTA ANA, CA
For more information call:
(714) 979-8220

FEATURES

- SILICON HIGH FORWARD CONDUCTANCE SWITCHING DIODE
- VOIDLESS* HERMETICALLY SEALED GLASS PACKAGE
- METALLURGICALLY BONDED (-1 TYPE)
  TX, TXV TYPES AVAILABLE PER MIL-S-19500/403

* EXCLUDES DO-35 DUMET CONSTRUCTION OPTION.

MILITARY SWITCHING DIODES

MAXIMUM RATINGS

Operating Temperature: -65°C to +175°C
Storage Temperature: -65°C to +200°C
Surge Current: 4 Amps ($t_p = 1\mu s$)
Leakage Current: 100nA @ 75V, 25°C.

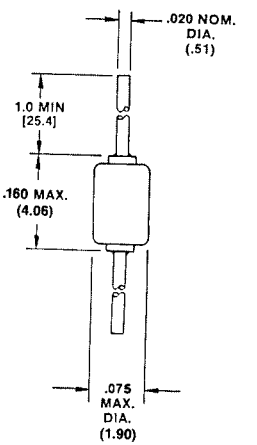

FIGURE 1
PACKAGE DO-35

ELECTRICAL CHARACTERISTICS

at 25°C unless otherwise specified.

$V_{(BR)}$	V_{RWM} (working)	Io (note 1)	i_f (surge) (1 sec)	i_f (surge) (1 μsec)	T_{OP}	T_{STG}
Vdc	V(pk)	mAdc	A	A	°C	°C
80	75	300	0.5	4.0	-65 to +175	-65 to +200

CAPACITANCE V_R = 0 Volts V_{sig} = 50 mVpp 100KHz≤f≤1 MHz	V_{f1} @ I_F = 250μAdc	V_{f2} @ I_F = 1.0mA	V_{f3} @ I_F = 10mA	V_{f4} @ I_F = 20mA	V_{f5} @ I_F = 300mA (pulse)	t_{rr} @ I_F = I_{R2} 10mAdc R_L = 100 ohms
pF	Vdc	Vdc	Vdc	Vdc	Vdc	ns
4 max.	.47 - .56	.52 - .60	.64 - .72	.67 - .77	1.1 max.	6.0 max.

NOTE 1: DERATE 2.0 mAdc/°C For T_A Above 25°C.

MECHANICAL CHARACTERISTICS

CASE: Hermetically sealed hard glass case.

LEAD MATERIAL: Tinned copper clad steel.

MARKING: Body painted, alpha numeric.

POLARITY: Cathode band.